L Number	Hits	Search Text	DB	Time stamp
- Number	26	(pix I and TFT and display and driver and	USPAT;	2003/01/29
		substrate and gat and lectr de and	US-PGPUB;	10:49
		(chann I r (channel n ar f rming) r	EPO; JPO;	
		channel-forming)).clm.	DERWENT;	
		<b>3</b> //	IBM_TDB	
	612	(pixel near TFT).ti,ab,clm.	USPAT;	2003/01/29
	0.2	(pinor nous or syndyamyonin	US-PGPUB;	10:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	23	((pixel near TFT).ti,ab,clm.) and (driver	USPAT;	2003/01/29
		near5 TFT).clm.	US-PGPUB:	10:53
			EPO; JPO;	10.00
			DERWENT;	
			IBM_TDB	
	26696	(tft or (thin near film near transistor)).ab.	USPAT;	2003/01/29
	20000	(11. 5) (11.111 11.00) Hilli Heal Hallsistol //iabi	US-PGPUB;	10:55
			EPO; JPO;	10.00
1			DERWENT;	
			IBM TDB	
	2959	((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
	2909		US-PGPUB;	10:56
		and (tft or (thin near film near		10:50
		transistor)).clm.	EPO; JPO;	
			DERWENT;	
	4000		IBM_TDB	0000104100
	1332	(((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
		and (tft or (thin near film near	US-PGPUB;	10:56
		transistor)).clm.) and (pixel).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/04/00
-	869	((((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
		and (tft or (thin near film near	US-PGPUB;	10:56
		transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.	DERWENT;	
			IBM_TDB	
	684	(((((tft or (thin near film near transistor)).ab.)	USPAT;	2003/01/29
		and (tft or (thin near film near	US-PGPUB;	10:57
		transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.	DERWENT;	
			IBM_TDB	
	653	((((((tft or (thin near film near	USPAT;	2003/01/29
		transistor)).ab.) and (tft or (thin near film	US-PGPUB;	10:57
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
1		(pixel).ab.) and gate.clm.) and	DERWENT;	
		electrode.clm.	IBM_TDB	
	75	(((((((tft or (thin near film near	USPAT;	2003/01/29
		transist r)).ab.) and (tft r (thin near film	US-PGPUB;	10:57
		near transist r)).clm.) and (pix l).clm.) and	EPO; JPO;	
		(pix I).ab.) and gate.clm.) and	DERWENT;	
		I ctr de.clm.) and driv r.clm.	IBM_TDB	

•	189	((((((tft r (thin near film n ar	USPAT;	2003/01/29
		transist r)).ab.) and (tft r (thin near film	US-PGPUB;	10:57
		n ar transist r)).clm.) and (pix l).clm.) and	EPO; JP ;	
		(pix I).ab.) and gate.clm.) and	DERWENT;	
		el ctrod .clm.) and driv r	IBM_TDB	ł
	581	(((((((tft or (thin near film near	USPAT;	2003/01/29
		transist r)).ab.) and (tft or (thin n ar film	US-PGPUB;	10:58
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.) and	DERWENT;	ļ
		electrode.clm.) and (display or displaying or	IBM_TDB	
	ì	displayed).ti,ab,clm.		l
	413	(((((((tft or (thin near film near	USPAT;	2003/01/29
		transistor)).ab.) and (tft or (thin near film	US-PGPUB;	10:59
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.) and	DERWENT;	
		electrode.clm.) and (display or displaying or	IBM_TDB	:
		displayed).ti,ab,clm.) and (channel or		
		(channel near forming) or channel-forming)		
	105	((((((((tft or (thin near film near	USPAT;	2003/01/29
		transistor)).ab.) and (tft or (thin near film	US-PGPUB;	11:00
		near transistor)).clm.) and (pixel).clm.) and	EPO; JPO;	
		(pixel).ab.) and gate.clm.) and	DERWENT;	į
		electrode.clm.) and (display or displaying or	IBM_TDB	
		displayed).ti,ab,clm.) and (channel or		
		(channel near forming) or channel-forming))		
		and capacitor.clm.		

L	Hits	Search Text	DB	Tim stamp
Number -	1442	(((display r displaying r display d r pix l)	USPAT;	2003/01/29
		near20 (substrat ) n ar20 driv r)) and (tft or	US-PGPUB;	11:18
		(thin n ar film near transistor))	EPO; JPO;	
		(	DERWENT;	
			IBM_TDB	
	668	(((display or displaying or displayed or pixel)	USPAT;	2003/01/29
		near20 (substrate) near20 driver)) and (tft or	US-PGPUB;	11:19
		(thin near film near transistor)).clm.	EPO; JPO;	
		(unit itola itimi itola di anticioto),	DERWENT;	
			IBM_TDB	
	573	((((display or displaying or displayed or	USPAT;	2003/01/29
	0.0	pixel) near20 (substrate) near20 driver)) and	US-PGPUB;	11:20
		(tft or (thin near film near transistor)).clm.)	EPO; JPO;	
		and (lcd or display or (liquid near	DERWENT;	
		crystal)).ti,ab,clm.	IBM TDB	
	559	(((((display or displaying or displayed or	USPAT;	2003/01/29
	333	pixel) near20 (substrate) near20 driver)) and	US-PGPUB;	11:20
		(tft or (thin near film near transistor)).clm.)	EPO; JPO;	20
		and (lcd or display or (liquid near	DERWENT;	
1		crystal)).ti,ab,clm.) and (display or	IBM_TDB	
		displaying or displayed).ti,ab,clm.	15111_155	
į	281	((((((display or displaying or displayed or	USPAT;	2003/01/29
	201	pixel) near20 (substrate) near20 driver)) and	US-PGPUB;	11:20
:		(tft or (thin near film near transistor)).clm.)	EPO; JPO;	11.20
		and (lcd or display or (liquid near	DERWENT;	
1		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	
		crystal)).ti,ab,clm.) and (display or	IBM_IDB	
		displaying or displayed).ti,ab,clm.) and		
	244	(substrate).ab.	USPAT;	2003/01/29
	244	(((((((display or displaying or displayed or pixel) near20 (substrate) near20 driver)) and	US-PGPUB;	11:21
		(tft or (thin near film near transistor)).clm.)	EPO; JPO;	11.21
		and (lcd or display or (liquid near	DERWENT;	
İ		crystal)).ti,ab,clm.) and (display or	IBM_TDB	
		displaying or displayed).ti,ab,clm.) and	IBM_IBB	
		(substrate).ab.) and (channel or (channel		
	217	near forming)) (((((((display or displaying or displayed or	USPAT;	2003/01/29
-	217	pixel) near20 (substrate) near20 driver)) and	US-PGPUB;	11:22
		(tft or (thin near film near transistor)).clm.)	EPO; JPO;	11172
			DERWENT;	
		and (lcd or display or (liquid near	IBM_TDB	
		crystal)).ti,ab,clm.) and (display or	IBINI_I DB	
		displaying or displayed).ti,ab,clm.) and	[1]	
		(substrate).ab.) and (channel or (channel		
		near forming))) and ((display or displaying or		
		displayed or pixel) near10 (substrate)		ĺ
		near10 driver)	1	

•	67	(((((((display or displaying r display d r	USPAT;	2003/01/29
		pix I) n ar20 (substrat ) near20 driver)) and	US-PGPUB;	11:22
		(tft r (thin near film n ar transist r)). lm.)	EPO; JPO;	I
		and (Icd r display r (liquid n ar	DERWENT;	
		crystal)).ti,ab,clm.) and (display r	IBM_TDB	Ì
		displaying r display d).ti,ab,clm.) and		
		(substrat ).ab.) and (chann I or (channel		
		near forming))) and ((display or displaying or		
		displayed or pixel) near10 (substrate)		
		near10 driver).ti.ab.clm.		

L Number	Hits	Search Text	DB	Time stamp
•	20	((pix I n ar100 (drive or driv r) near100 (tft	USPAT;	2003/01/29
		r (thin n ar film n ar transist r))) near100	US-PGPUB;	16:39
		gate near100   ctrode near100 (conducting	EPO; JPO;	
		r c nductiv r m tal or conductor or	DERWENT;	
		layer)).clm.	IBM_TDB	
İ	18	(((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
		or (thin near film near transistor))) near100	US-PGPUB;	16:37
		gate near100 electrode near100 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer)).clm.) and (size or dense or density or densely)	IBM_TDB	
	18	(((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
		or (thin near film near transistor))) near100	US-PGPUB;	16:38
		gate near100 electrode near100 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer)).clm.) and (size or dense or density or	IBM_TDB	
		densely or compact or packed)		
	2	(((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
		or (thin near film near transistor))) near100	US-PGPUB;	16:38
		gate near100 electrode near100 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer)).clm.) and (size or dense or density or	IBM_TDB	
		densely or compact or packed).ti,ab,clm.		
	5	((pixel near100 (drive or driver) near100 (tft	USPAT;	2003/01/29
		or (thin near film near transistor))) near100	US-PGPUB;	16:41
		gate near100 electrode near100 (conducting	EPO; JPO;	
		or conductive or metal or conductor or	DERWENT;	
		layer) near100 (substrate) near100 (channel	IBM_TDB	
		or channel-forming)).clm.		
	5	((pixel near200 (drive or driver) near200 (tft	USPAT;	2003/01/29
		or (thin near film near transistor))) near200	US-PGPUB;	16:44
		gate near200 electrode near200 (conducting	EPO; JPO;	
ļ		or conductive or metal or conductor or	DERWENT;	
1		layer) near200 (substrate) near200 (channel	IBM_TDB	
		or channel-forming)).clm.		
	8	((pixel near200 (drive or driver) near200 (tft	USPAT;	2003/01/31
		or (thin near film near transistor))) near200	US-PGPUB;	13:40
		gate near200 electrode near200 (conducting	EPO; JPO;	
b 7		or conductive or metal or conductor or	DERWENT;	
		layer) near200 (substrate) near200 (channel or channel-forming)).ti,ab,clm.	IBM_TDB	
	126674	pixel.ti,ab,clm.	USPAT;	2003/01/31
		-	US-PGPUB;	13:48
			EPO; JPO;	AV V
			DERWENT;	
V A			IBM_TDB	
	9544	pixel.ti,ab,clm. and (tft or (thin n ar film	USPAT;	2003/01/31
		near transist r)).ti,ab,clm.	US-PGPUB;	13:51
		,,,,,,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

- 205	(pix l.ti,ab,clm. and (tft r (thin n ar film	USPAT;	2003/01/31
	near transist r)).ti,ab,clm.) and (driver or	US-PGPUB;	13:49
	drive).ti,ab,clm.	EPO; JPO;	
		DERWENT;	
		IBM_TDB	
- 864	((pix l.ti,ab,clm. and (tft or (thin n ar film	USPAT;	2003/01/31
	n ar transist r)).ti,ab,clm.) and (driv r	US-PGPUB;	13:50
	drive).ti,ab,clm.) and (gate and	EPO; JPO;	
	electrode).ti,ab,clm.	DERWENT;	
		IBM_TDB	
_ 274	(((pixel.ti,ab,clm. and (tft or (thin near film	USPAT;	2003/01/31
	near transistor)).ti,ab,clm.) and (driver or	US-PGPUB;	13:50
	drive).ti,ab,clm.) and (gate and	EPO; JPO;	
	electrode).ti,ab,clm.) and	DERWENT;	
	(channel).ti,ab,clm.	IBM_TDB	
- 9		USPAT;	2003/01/31
- 3		US-PGPUB;	13:50
	near transistor)).ti,ab,clm.) and (driver or	1	13:50
	drive).ti,ab,clm.) and (gate and	EPO; JPO;	
	electrode).ti,ab,clm.) and	DERWENT;	
	(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
	and (dope or doped or doping or impurity or		
	dopant)).ti,ab,clm.		
- 7	, , ,	USPAT;	2003/01/31
	near transistor)).ti,ab,clm.) and (driver or	US-PGPUB;	13:51
	drive).ti,ab,clm.) and (gate and	EPO; JPO;	
	electrode).ti,ab,clm.) and	DERWENT;	
ŀ	(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
	and (dope or doped or doping or impurity or		
	dopant)).ti,ab,clm.) and (tft or (thin near film		
	near transistor)).ab.		
- 6	((((((pixel.ti,ab,clm. and (tft or (thin near film	USPAT;	2003/01/31
	near transistor)).ti,ab,clm.) and (driver or	US-PGPUB;	13:52
	drive).ti,ab,clm.) and (gate and	EPO; JPO;	
	electrode).ti,ab,clm.) and	DERWENT;	
	(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
	and (dope or doped or doping or impurity or	_	
	dopant)).ti,ab,clm.) and (tft or (thin near film		
	near transistor)).ab.) and (display or		:
	displaying or displayed).ti,ab,clm.		
. 4		USPAT;	2003/01/31
	film near transistor)).ti,ab,clm.) and (driver	US-PGPUB;	13:53
	or drive).ti,ab,clm.) and (gate and	EPO; JPO;	10.00
	electrode).ti,ab,clm.) and	DERWENT;	
	(channel).ti,ab,clm.) and (source and drain	IBM_TDB	
	and (dope or doped or doping or impurity or	10m_100	
	dopant)).ti,ab,clm.) and (tft or (thin near film		
			[3]
			1
	1 '		
	near transistor)).ab.) and (display or displaying or displayed).ti,ab,clm.) and (c nductiv or conducting or conduct r or lay r r m tal).ti,ab,clm.		

4	((((((((pix l.ti,ab,clm. and (tft r (thin n ar	USPAT;	2003/01/31
	film near transist r)).ti,ab,clm.) and (driv r	US-PGPUB;	13:54
:	or driv ).ti,ab,clm.) and (gate and	EPO; JPO;	
	el ctrod ).ti,ab,clm.) and	DERWENT;	
	(channel).ti,ab,clm.) and (s urc and drain	IBM_TDB	
	and (dop or d ped or doping r impurity or		
	dopant)).ti,ab,clm.) and (tft or (thin near film		
	near transistor)).ab.) and (display or		
	displaying or displayed).ti,ab,clm.) and		
	(conductive or conducting or conductor or		
	layer or metal).ti,ab,clm.) and		
	(substrate.ti,ab,clm.)		

	US-6365917-\$ r US-6335716-\$ r US-6323515-\$ r US-6278131-\$ r US-6271818-\$ or US-6236063-\$ or	US-PGPUB; EPO; JP ;	13:54
	US-6271818-\$ or US-6236063-\$ or		1
	· · · -	DERWENT	Į
	US-6147667-\$ r US-6146930-\$ r		
[	US-6137219-\$ r US-5767930-\$ r		
}	US-6498369-\$ or US-6490021-\$ or		
	US-6461899-\$ or US-6246454-\$ or		[
	US-5923997-\$ or US-6509939-\$ or		
	US-6500702-\$ or US-6495858-\$ or		1
	US-6493046-\$ or US-6417896-\$ or		
	US-6400424-\$ or US-6377322-\$ or		
	US-6356318-\$ or US-6351010-\$).did. or		
	(US-6346730-\$ or US-6307322-\$ or		
	US-6292237-\$ or US-6281957-\$ or		
	US-6281552-\$ or US-6259117-\$ or		
	US-6243146-\$ or US-6194837-\$ or		
	US-6175394-\$ or US-6118506-\$ or		
	US-6057896-\$ or US-6023074-\$ or		
	US-6011274-\$ or US-5990998-\$ or		
	US-5966190-\$ or US-5966189-\$ or		1
	US-5940151-\$ or US-5923310-\$ or		
	US-5920362-\$ or US-5920084-\$ or		
İ	US-5920082-\$ or US-5914762-\$ or		[
	US-5856858-\$ or US-5822026-\$ or		1
	US-5815226-\$ or US-5796448-\$ or		
	US-5784131-\$).did. or (US-5777700-\$ or		
	US-5763899-\$ or US-5760854-\$ or		
	US-5729308-\$ or US-5724107-\$ or		
	US-5714770-\$ or US-5694185-\$ or		
	US-5686976-\$ or US-5671027-\$ or		
	US-5650636-\$ or US-5641974-\$ or		
	US-5610738-\$ or US-5610736-\$ or		
	US-5546205-\$ or US-5526014-\$ or		
	US-5519521-\$ or US-5459596-\$ or		
	US-5402254-\$ or US-5235448-\$ or		
	US-5159476-\$ or US-5132820-\$ or		
	US-6504215-\$ or US-6486497-\$ or		
	US-6465268-\$ or US-6399933-\$ or		
	US-6380687-\$ or US-6346978-\$).did. or		
	(US-6300174-\$ or US-6288412-\$ or		
	US-6177301-\$ or US-6150692-\$ or		
	US-6136632-\$ or US-5969377-\$ or		
	US-5877514-\$ or US-5811837-\$ or		
	US-5798744-\$ or US-5789763-\$ or		
	US-5764320-\$ or US-5742075-\$ or		
	US-5707882-\$ or US-5656826-\$ or		
	US-5510807-\$ or US-5504348-\$ or		
	US-5426447-\$ r US-5313222-\$ r		
	US-5250931-\$ or US-4644338-\$ r		
1	US-6501096-\$ or US-5589406-\$ r		
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		US-6493046-\$ or US-6417896-\$ or US-6400424-\$ or US-6377322-\$ or US-6356318-\$ or US-6307322-\$ or US-6346730-\$ or US-6281957-\$ or US-6281552-\$ or US-6281957-\$ or US-6281552-\$ or US-6281957-\$ or US-6281552-\$ or US-6259117-\$ or US-6243146-\$ or US-6194837-\$ or US-6175394-\$ or US-6023074-\$ or US-6057896-\$ or US-590998-\$ or US-5966190-\$ or US-5966189-\$ or US-5940151-\$ or US-5920362-\$ or US-5920084-\$ or US-5920362-\$ or US-5920084-\$ or US-5920362-\$ or US-5815226-\$ or US-57777700-\$ or US-5763899-\$ or US-5760854-\$ or US-5763899-\$ or US-5724107-\$ or US-5763899-\$ or US-5724107-\$ or US-57614770-\$ or US-5641974-\$ or US-5610738-\$ or US-5641974-\$ or US-5519521-\$ or US-5641974-\$ or US-5519521-\$ or US-5252044-\$ or US-519521-\$ or US-5235448-\$ or US-519521-\$ or US-63486497-\$ or US-6304215-\$ or US-63486497-\$ or US-636036-\$ or US-6304215-\$ or US-63486497-\$ or US-636036-\$ or US-639933-\$ or US-636037-\$ or US-6300174-\$ or US-6346978-\$).did. or (US-6300174-\$ or US-6346978-\$).did. or (US-6300174-\$ or US-635692-\$ or US-6377514-\$ or US-6150692-\$ or US-6136632-\$ or US-5811837-\$ or US-5707882-\$ or US-5707882-\$ or US-5707882-\$ or US-5504348-\$ or US-55250931-\$ or US-5504348-\$ or US-570882-\$ or US-5504348-\$ or US-550931-\$ or US-5504348-\$ or US-55250931-\$ or U	US-6493046-\$ or US-6417896-\$ or US-6400424-\$ or US-6377322-\$ or US-6356318-\$ or US-6351010-\$).did. or (US-6346730-\$ or US-63617322-\$ or US-6292237-\$ or US-6281957-\$ or US-6281552-\$ or US-6259117-\$ or US-6243146-\$ or US-6194837-\$ or US-6057896-\$ or US-6023074-\$ or US-6057896-\$ or US-6923074-\$ or US-6051274-\$ or US-5990998-\$ or US-5966190-\$ or US-5966189-\$ or US-5960190-\$ or US-596084-\$ or US-5920362-\$ or US-5920084-\$ or US-5920362-\$ or US-5920084-\$ or US-5920082-\$ or US-5914762-\$ or US-5815226-\$ or US-5914762-\$ or US-5784131-\$).did. or (US-5777700-\$ or US-5784131-\$).did. or (US-5777700-\$ or US-5784131-\$).did. or (US-5777700-\$ or US-5763899-\$ or US-5760854-\$ or US-5784031-\$).did. or (US-5777700-\$ or US-5763899-\$ or US-5760854-\$ or US-5763899-\$ or US-5724107-\$ or US-576370-\$ or US-5641974-\$ or US-5610738-\$ or US-5641974-\$ or US-5610738-\$ or US-5641974-\$ or US-5540225-\$ or US-5526014-\$ or US-5549205-\$ or US-5526014-\$ or US-5549225-\$ or US-5235448-\$ or US-519976-\$ or US-5459596-\$ or US-6300174-\$ or US-6346978-\$).did. or (US-6300174-\$ or US-6346978-\$).did. or (US-6300174-\$ or US-6346978-\$).did. or US-674320-\$ or US-6288412-\$ or US-674320-\$ or US-56809377-\$ or US-5798744-\$ or US-5899933-\$ or US-6376820-\$ or US-5789763-\$ or US-5707882-\$ or US-556826-\$ or US-5510807-\$ or US-556826-\$ or US-550931-\$ or US-5589406-\$ r US-550931-\$ or US-5589406-\$ r US-63406240-\$ or US-6346978-\$ \).did. or US-56492640-\$ or US-5898406-\$ r US-650998-\$ or US-5504348-\$ or US-5510807-\$ or US-5504348-\$ or US-56496240-\$ or US-5898406-\$ r US-6496240-\$ or US-6348718-\$ or US-6496240-\$ or US-6348718-\$ or US-6496240-\$ or US-6448718-\$ or US-6496881488305-\$ on US-66416771-\$ r

i j	51	((US-6480179-\$ r US-6476788-\$ r	USPAT; US-PGPUB;	2003/01/31 13:55
		US-6365917-\$ r US-6335716-\$ r US-6323515-\$ or US-6278131-\$ r	EPO; JPO;	13:35
		US-6271818-\$ r US-6236063-\$ r	DERWENT;	
		US-6147667-\$ or US-6146930-\$ or	IBM_TDB	
		US-6137219-\$ or US-5767930-\$ or	10111_100	
		US-6498369-\$ or US-6490021-\$ or		
		US-6461899-\$ or US-6246454-\$ or		
		US-5923997-\$ or US-6509939-\$ or US-6500702-\$ or US-6495858-\$ or		
		US-6493046-\$ or US-6417896-\$ or US-6400424-\$ or US-6377322-\$ or		
		US-6356318-\$ or US-6351010-\$).did. or		
		(US-6346730-\$ or US-6307322-\$ or US-6292237-\$ or US-6281957-\$ or		
		US-6292237-\$ or US-625917-\$ or US-6281552-\$ or US-6259117-\$ or		
				1
		US-6243146-\$ or US-6194837-\$ or		
		US-6175394-\$ or US-6118506-\$ or		
4		US-6057896-\$ or US-6023074-\$ or		
		US-6011274-\$ or US-5990998-\$ or		1
		US-5966190-\$ or US-5966189-\$ or		
		US-5940151-\$ or US-5923310-\$ or		
		US-5920362-\$ or US-5920084-\$ or		
		US-5920082-\$ or US-5914762-\$ or		
		US-5856858-\$ or US-5822026-\$ or		
		US-5815226-\$ or US-5796448-\$ or		
		US-5784131-\$).did. or (US-5777700-\$ or		
		US-5763899-\$ or US-5760854-\$ or		
		US-5729308-\$ or US-5724107-\$ or		
		US-5714770-\$ or US-5694185-\$ or		
		US-5686976-\$ or US-5671027-\$ or		
		US-5650636-\$ or US-5641974-\$ or US-5610738-\$ or US-5610736-\$ or		
		US-5610738-\$ or US-5610736-\$ or		
		US-55462U5-\$ or US-5526U14-\$ or US-5519521-\$ or US-5459596-\$ or		
			3.1	
		US-5402254-\$ or US-5235448-\$ or		
	U	US-5159476-\$ or US-5132820-\$ or		
		US-6504215-\$ or US-6486497-\$ or		
		US-6465268-\$ or US-6399933-\$ or		
		US-6380687-\$ or US-6346978-\$).did. or		
		(US-6300174-\$ or US-6288412-\$ or		
		US-6177301-\$ or US-6150692-\$ or		
		US-6136632-\$ or US-5969377-\$ or		-
		US-5877514-\$ or US-5811837-\$ or		Francisco
		US-5798744-\$ or US-5789763-\$ or		1
		US-5764320-\$ or US-5742075-\$ or		1
		US-5707882-\$ or US-5656826-\$ or		
		US-5510807-\$ or US-5504348-\$ or		
		US-5426447-\$ or US-5313222-\$ r		
		US-5250931-\$ r US-4644338-\$ r		
		US-6501096-\$ or US-5589406-\$ r		
		US-6496240-\$ r US-6448718-\$ r	0 67	
		US-6433852-\$ r US-6411273-\$ or	9_1	
		US-6407508-\$).did. or (US-6346718-\$ r		
		348-83249986 op45-6307528-\$ r		
IADDEL OF	et/workense	се <b>Ы6951976005_бас</b> еЫ% 6166711-\$ г	1	I

-	54	((pixel and TFT and display and (drive r	USPAT;	2003/02/03
		driver) and substrate and gat and el ctr d	US-PGPUB;	15:08
		and (channel or (chann I near f rming) r	EPO; JPO;	
		channel-forming) and (c nducting r	DERWENT;	
		c nduct or conductiv or metal or	IBM_TDB	
		lay r))).ti,ab,clm. and (capacitor or capacitance)		
	34	(((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	14:53
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance) ) and (dope or doping or doped		
		or dopant or impurity).ti,ab,clm.		
	21	((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	14:53
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance) ) and (dope or doping or doped		
		or dopant or impurity).ti,ab,clm.) and		
		(conduct or conducting or conductive or		
		metal).ti,ab,clm.		

L Number	Hits	S arch T xt	DB	Tim stamp
• Number	22	(((pixel and TFT and display and (driv or driver) and substrate and gat and lectr de and (chann I or (chann I near forming) r chann I-f rming) and (c nducting r c nduct r c nductive or m tal or layer))).ti,ab,clm. and (capacitor or capacitance)) and (nitrogen or tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 15:17
-	22	copper).clm.  ((((pixel and TFT and display and (drive or driver) and substrate and gate and electrode and (channel or (channel near forming) or channel-forming) and (conducting or conduct or conductive or metal or layer))).ti,ab,clm. and (capacitor or capacitance)) and (nitrogen or tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper).clm.) and substrate.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 15:12
	22	(((((pixel and TFT and display and (drive or driver) and substrate and gate and electrode and (channel or (channel near forming) or channel-forming) and (conducting or conduct or conductive or metal or layer))).ti,ab,clm. and (capacitor or capacitance)) and (nitrogen or tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper).clm.) and substrate.ti,ab,clm.) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 15:12
-	20	(drive or driver).ti,ab,clm.  ((((((pixel and TFT and display and (drive or driver) and substrate and gate and electrode and (channel or (channel near forming) or channel-forming) and (conducting or conduct or conductive or metal or layer))).ti,ab,clm. and (capacitor or capacitance)) and (nitrogen or tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper).clm.) and substrate.ti,ab,clm.) and (drive or driver).ti,ab,clm.) and ((drive or driver) same (tft or (thin near film near	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/03 15:14

	18	(((((((pixel and TFT and display and (drive r	USPAT;	2003/02/03
		driv r) and substrate and gate and el ctrode	US-PGPUB;	15:21
		and (channel r (channel near f rming) r	EPO; JPO;	
		chann I-f rming) and (c nducting r	DERWENT;	
		c nduct or conductive r metal r	IBM_TDB	
		lay r))).ti,ab,clm. and (capacitor r		
		capacitance)) and (nitr gen r tantalum r		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm. ) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
		driver) same (tft or (thin near film near		
ĺ		transistor))).ti,ab,clm.) and (pixel same (tft	-	
		or (thin near film near transistor))).ti,ab,clm.		
	18	(((((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
ŀ		driver) and substrate and gate and electrode	US-PGPUB;	15:14
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
1		conduct or conductive or metal or	IBM_TDB	1
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm. ) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		İ
		driver) same (tft or (thin near film near		1
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near20 (tft or (thin near film near		
		transistor))).ti,ab,clm.		
	18	((((((((pixel and TFT and display and (drive	USPAT:	2003/02/03
		or driver) and substrate and gate and	US-PGPUB;	15:20
		electrode and (channel or (channel near	EPO; JPO;	10.20
		forming) or channel-forming) and	DERWENT;	İ
		(conducting or conduct or conductive or	IBM_TDB	
		metal or layer))).ti,ab,clm. and (capacitor or		1
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm. ) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or		
,		driver) same (tft or (thin near film near	_4.	
		wiiver, saine the or thin hear linn heaf	1	1
		transistor))) ti ah alm ) and (nival same (466		
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		
·		or (thin near film near transistor))).ti,ab,clm.) and ((drive or driver)		
		or (thin near film near transistor))).ti,ab,clm.) and ((drive or driver) near20 (tft or (thin near film near		
		or (thin near film near transistor))).ti,ab,clm.) and ((drive or driver)		

•	18	((((((((pixel and TFT and display and (drive	USPAT;	2003/02/03
		or driver) and substrat and gate and	US-P PUB;	15:14
		el tr de and (channel or (chann i near	EPO; JPO;	
		forming) r chann l-f rming) and	DERWENT;	
		(c nducting or conduct or c nductive r	IBM_TDB	
		m tal r lay r))).ti,ab,clm. and (capacitor or		
		capacitanc )) and (nitrogen r tantalum or		
		titanium or tungsten or ta or ti or mo or	44	
		molybdenum or al or cu or aluminum or	4	,
		copper).clm. ) and substrate.ti,ab,clm.) and		1
		(drive or driver).ti,ab,clm.) and ((drive or		
		driver) same (tft or (thin near film near	:	
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near20 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
	1	near100 (tft or (thin near film near		
		transistor))).ti,ab,clm.		
-	18	(((((((((pixel and TFT and display and (drive	USPAT;	2003/02/03
		or driver) and substrate and gate and	US-PGPUB;	15:14
		electrode and (channel or (channel near	EPO; JPO;	
		forming) or channel-forming) and	DERWENT;	
		(conducting or conduct or conductive or	IBM_TDB	
		metal or layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper).clm.) and substrate.ti,ab,clm.) and		
		(drive or driver).ti,ab,clm.) and ((drive or	j	
		driver) same (tft or (thin near film near		- 79
		transistor))).ti,ab,clm.) and (pixel same (tft		
		or (thin near film near		·
		transistor))).ti,ab,clm.) and ((drive or driver)	•	
		near20 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)	, i	
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and ((drive or driver)		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.		
-	53	(((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:19
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen r tantalum or		
		titanium r tungst n r ta or ti or mo or		
		molybd num ral or cu or aluminum r		
		copp r)		

•	53	((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
1		driver) and substrat and gat and I ctr de	US-P PUB;	15:20
1		and (channel or (chann I near f rming) or	EP ; JPO;	1
		chann I-f rming) and (conducting r	DERWENT;	
		c nduct r conductiv r m tal or	IBM TDB	
i		lay r))).ti,ab,clm. and (capacit r or		
		capacitance)) and (nitr gen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper) ) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))		0
	46	(((((pixel and TFT and display and (drive or	USPAT;	2003/02/03
		driver) and substrate and gate and electrode	US-PGPUB;	15:24
ŀ		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
<u> </u>		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
İ		copper) ) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))) and (pixel		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.		
	36	((((((pixel and TFT and display and (drive or	USPAT:	2003/02/03
	30		,	15:25
		driver) and substrate and gate and electrode	US-PGPUB;	15:25
		and (channel or (channel near forming) or	EPO; JPO;	
		channel-forming) and (conducting or	DERWENT;	
		conduct or conductive or metal or	IBM_TDB	
		layer))).ti,ab,clm. and (capacitor or		
		capacitance)) and (nitrogen or tantalum or		
		titanium or tungsten or ta or ti or mo or		
		molybdenum or al or cu or aluminum or		
		copper) ) and ((drive or driver) near10 (tft or		
		(thin near film near transistor)))) and (pixel		
		near10 (tft or (thin near film near		
		transistor))).ti,ab,clm.) and (pixel same		
		(display or displaying) same (driver or drive)		
1		i tulopiav vi ulopiavilju) salije tulive: vi prive:	4	

((((((pixel and TFT and display and (driv or driver) and substrate and gate and lectrode and (chann I r (channel near forming) r channel-forming) and (conducting r conduct or c nductive r metal r lay r))).ti,ab,clm. and (capacitor or capacitanc )) and (nitrog n r tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel near10 (tft or (thin near film near	
and (chann I r (channel near forming) r channel-forming) and (conducting r conduct or c nductive r metal r lay r))).ti,ab,clm. and (capacitor or capacitanc )) and (nitrog n r tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
channel-forming) and (conducting r conduct or c nductive r metal r lay r))).ti,ab,clm. and (capacitor or capacitanc )) and (nitrog n r tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
conduct or c nductive r metal r lay r))).ti,ab,clm. and (capacitor or capacitanc )) and (nitrog n r tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
lay r))).ti,ab,clm. and (capacitor or capacitanc )) and (nitrog n r tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
capacitanc )) and (nitrog n r tantalum or titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
titanium or tungsten or ta or ti or mo or molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
molybdenum or al or cu or aluminum or copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
copper) ) and ((drive or driver) near10 (tft or (thin near film near transistor)))) and (pixel	
(thin near film near transistor)))) and (pixel	
(thin near film near transistor)))) and (pixel	
	,
	t
transistor))).ti,ab,clm.) and (pixel same	İ
(display or displaying) same (driver or drive)	
same substrate same (tft or (thin near film	
near transistor)))	İ
	13
	,,
	ļ
and (channel or (channel near forming) or EPO; JPO;	į
channel-forming) and (conducting or DERWENT;	
conduct or conductive or metal or IBM_TDB	į
layer))).ti,ab,clm. and (capacitor or	
capacitance)) and (nitrogen or tantalum or	
titanium or tungsten or ta or ti or mo or	i
molybdenum or al or cu or aluminum or	!
copper) ) and ((drive or driver) near10 (tft or	i
(thin near film near transistor)))) and (pixel	ľ
near10 (tft or (thin near film near	
transistor))).ti,ab,clm.) and (pixel near20	İ
(display or displaying) near20 (driver or	ļ
drive) near20 substrate near20 (tft or (thin	
near film near transistor)))	i
- 13 ((((((pixel and TFT and display and (drive or USPAT; 2003/02/0	3 1
driver) and substrate and gate and electrode US-PGPUB; 15:29	
and (channel or (channel near forming) or EPO; JPO;	
channel-forming) and (conducting or DERWENT;	
conduct or conductive or metal or IBM_TDB	
layer))).ti,ab,clm. and (capacitor or	1
capacitance)) and (nitrogen or tantalum or	
titanium or tungsten or ta or ti or mo or	1
molybdenum or al or cu or aluminum or	1
copper) ) and ((drive or driver) near10 (tft or	ļ
(thin near film near transistor)))) and (pixel	
near10 (tft or (thin near film near	
transistor))).ti,ab,clm.) and (pixel same	
(display or displaying) same (driver or drive)	
same substrate same (tft or (thin near film	•
near transistor))).ti,ab,clm.	_
- 93 (pix I near20 (display or displaying) n ar20 USPAT; 2003/02/0	13
(driv r or driv ) n ar20 substrat near20 (tft   US-PGPUB;   15:32	
r (thin n ar film n ar transistor))).ti,ab,clm. EPO; JPO;	
DERWENT;	
IBM_TDB	

•	8	((pix I n ar20 (display or displaying) n ar20	USPAT;	2003/02/03
		(driver r drive) n ar20 substrate n ar20 (tft	US-PGPUB;	15:34
		or (thin n ar film near	EPO; JPO;	
		transist r))).ti,ab,clm.) and (gate and s urce	DERWENT;	
		and drain and channel).ti,ab,clm.	IBM_TDB	1
	2	((pix I n ar20 (display or displaying) n ar20	USPAT;	2003/02/03
		(driv r r driv ) near20 substrat n ar20 (tft	US-P PUB;	15:35
		or (thin near film near	EPO; JPO;	
		transistor))).ti,ab,clm.) and (tantalum or	DERWENT;	
		tungsten or titanium or molybdenum).ti,ab,clm.	IBM_TDB	
	14	((pixel near20 (display or displaying) near20	USPAT;	2003/02/03
		(driver or drive) near20 substrate near20 (tft	US-PGPUB;	15:38
		or (thin near film near	EPO; JPO;	
		transistor))).ti,ab,clm.) and (tantalum or	DERWENT;	
		tungsten or titanium or molybdenum)	IBM_TDB	

L	Hits	S arch T xt	DB	Time stamp
Numb r	631	(tantalum r titanium r tungsten r m lybd num r ta r ti or m ).clm. and (tft r (thin n ar film n ar transist r)).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/02/04 13:32
	539	((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft	IBM_TDB USPAT; US-PGPUB;	2003/02/04 13:32
		or (thin near film near transistor)).ab.) and substrate.clm.	EPO; JPO; DERWENT; IBM TDB	13.32
	471	(((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft or (thin near film near transistor)).ab.) and substrate.clm.) and (tft or (thin near film near transistor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/04 13:32
	52	((((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft or (thin near film near transistor)).ab.) and substrate.clm.) and (tft or (thin near film near transistor)).clm.) and (drive or driver).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/04 13:32
	33	(((((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft or (thin near film near transistor)).ab.) and substrate.clm.) and (tft or (thin near film near transistor)).clm.) and (drive or driver).clm.) and (nitrogen or N or argon or Ar or hydrogen or H).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/04 13:33
	25	((((((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft or (thin near film near transistor)).ab.) and substrate.clm.) and (tft or (thin near film near transistor)).clm.) and (drive or driver).clm.) and (nitrogen or N or argon or Ar or hydrogen or H).clm.) and (display or pixel).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/04 13:34
	17	(((((((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft or (thin near film near transistor)).ab.) and substrate.clm.) and (tft or (thin near film near transistor)).clm.) and (drive or driver).clm.) and (nitrogen or N or argon or Ar or hydrogen or H).clm.) and (display or pixel).clm.) and (aluminum or al or copper or cu).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/04 13:34

•	14	(((((((tantalum r titanium r tungsten r	USPAT;	2003/02/04
		m lybd num or ta or ti r mo).clm. and (tft or (thin n ar film n ar transistor)).ab.) and substrat .clm.) and (tft r (thin near film	US-P PUB; EPO; JPO; DERWENT;	13:36
		n ar transist r)).clm.) and (driv r driv r).clm.) and (nitrogen or N or argon or	IBM_TDB	
		Ar or hydrog n or H).clm.) and (display r pixel).clm.) and (aluminum or al or copper or		
		cu).clm.) and ((drive or driver) same (display or pixel) same substrate).clm.		
•	12	((((((((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft	USPAT; US-PGPUB;	2003/02/04 13:40
		or (thin near film near transistor)).ab.) and substrate.clm.) and (tft or (thin near film near transistor)).clm.) and (drive or	EPO; JPO; DERWENT; IBM_TDB	
		driver).clm.) and (nitrogen or N or argon or Ar or hydrogen or H).clm.) and (display or	IBM_19B	
		pixel).clm.) and (aluminum or al or copper or cu).clm.) and ((drive or driver) near10		
	5	(display or pixel) near10 substrate).clm. ((((((((tantalum or titanium or tungsten or	USPAT;	2003/02/04
-	3	molybdenum or training or tungsten or molybdenum or ta or ti or mol.clm. and (tft or (thin near film near transistor)).ab.) and	US-PGPUB; EPO; JPO;	13:38
		substrate.clm.) and (tft or (thin near film	DERWENT;	
		near transistor)).clm.) and (drive or driver).clm.) and (nitrogen or N or argon or	IBM_TDB	
		Ar or hydrogen or H).clm.) and (display or pixel).clm.) and (aluminum or al or copper or		·
		cu).clm.) and ((drive or driver) near10 (display or pixel) near10 substrate).clm.)		
		and (conductor or conducting or conducter or conductor or conductive).clm.		
	5	((((((((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft	USPAT; US-PGPUB;	2003/02/04 13:39
		or (thin near film near transistor)).ab.) and substrate.clm.) and (tft or (thin near film	EPO; JPO; DERWENT;	
		near transistor)).clm.) and (drive or	IBM_TDB	-
		driver).clm.) and (nitrogen or N or argon or Ar or hydrogen or H).clm.) and (display or		
		pixel).clm.) and (aluminum or al or copper or cu).clm.) and ((drive or driver) near10		
		(display or pixel) near10 substrate).clm.)		
		and (conductor or conducting or conducter or conductor or conductive or conduct).clm.		
•	296	((tantalum or titanium or tungsten or molybdenum or ta or ti or mo).clm. and (tft	USPAT; US-PGPUB;	2003/02/04 13:39
		or (thin near film near transistor)).ab.) and (conductor or conducting or conducter or	EPO; JPO; DERWENT;	
		c nduct rorc nductive or conduct).clm.	IBM_TDB	

•	11	(((tantalum or titanium or tungsten or	USPAT;	2003/02/04
		molybd num or tarti or mo).clm. and (tft	US-PGPUB;	13:44
		or (thin near film n ar transist r)).ab.) and	EPO; JPO;	
		(conductor or c ndu ting or c nduct r or	DERWENT;	
		conduct rorc nductive rconduct).clm.)	IBM_TDB	
		and ((drive r driver) near10 (display r		ļ
		pix I) n ar10 substrat ).clm.	İ	
•	160	((tft or (thin near film near transistor)) same	USPAT;	2003/02/04
		(pixel) same display same (drive or	US-PGPUB;	13:46
		driver)).clm.	EPO; JPO;	 
		<i>"</i>	DERWENT;	
			IBM_TDB	
•	93	(((tft or (thin near film near transistor)) same	USPAT;	2003/02/04
		(pixel) same display same (drive or	US-PGPUB;	13:46
		driver)).clm.) and (gate and electrode).clm.	EPO; JPO;	
		and the time time the time the time the time the time the time the time the time the time the time the	DERWENT:	
			IBM_TDB	
_	36	((((tft or (thin near film near transistor))	USPAT;	2003/02/04
•	30	same (pixel) same display same (drive or	US-PGPUB;	13:47
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	13.47
		and channel.clm.		
		and channel.cim.	DERWENT;	
		/////AEA an /Abrim ma Ether A A	IBM_TDB	2002/02/24
•	32	(((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:48
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
	·	near10 (pixel or display)).clm.	IBM_TDB	
1	13	(((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:52
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display) near10	IBM_TDB	
		substrate).clm.		
•	10	(((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:52
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display) near10	IBM_TDB	
		substrate).clm.) and (tantalum or titanium or		
		tungsten or molybdenum or ta or ti or mo)		
•	8	((((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:51
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display) near10	IBM_TDB	
		substrate).clm.) and (tantalum or titanium or		
		tungsten or molybdenum or ta or ti or mo))		
		and (conductor or conduct or conducting or		d co
		c nductive)		
	1	t inductive)	I	1

•	8	(((((tft r (thin n ar film n ar transistor))	USPAT;	2003/02/04
		same (pixel) same display same (driv r	US-PGPUB;	13:54
		driver)).clm.) and (gate and electrod ).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive r driver)	DERWENT;	
		n ar5 (pix I r display) near5 substrat ).clm.	IBM_TDB	
	7	(((((tft r (thin n ar film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:52
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near5 (pixel or display) near5	IBM_TDB	
		substrate).clm.) and (tantalum or titanium or tungsten or molybdenum or ta or ti or mo)		
	13	(((((tft or (thin near film near transistor))	USPAT;	2003/02/04
		same (pixel) same display same (drive or	US-PGPUB;	13:54
		driver)).clm.) and (gate and electrode).clm.)	EPO; JPO;	
		and channel.clm.) and ((drive or driver)	DERWENT;	
		near10 (pixel or display) near10	IBM_TDB	
		substrate).clm.	32332100	